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# FAN2108 — TinyBuck™ 3-24 V Input, 8 A, High-Efficiency, Integrated Synchronous Buck Regulator

## Features

- Wide Input Voltage Range: 3 V-24 V
- Wide Output Voltage Range: 0.8 V to 80%  $V_{IN}$
- 8 A Output Current
- Programmable Frequency Operation: 200 KHz to 600 KHz
- Over 95% Peak Efficiency
- Integrated Schottky Diode on Low-side MOSFET Boosts Efficiency
- Internal Bootstrap diode
- Power-Good Signal
- Pre-Bias Startup
- Accepts Ceramic Capacitors on Output
- External Compensation for Flexible Design
- Input Under-Voltage Lockout
- Programmable Current Limit
- Under-Voltage, Over-Voltage, and Thermal Shutdown Protections
- Internal Soft-Start
- 5 x 6 mm, 25-Pin, 3-Pad MLP Package

## Applications

- Servers
- Point-of-Load Regulation
- High-End Computing Systems
- Graphics Cards
- Battery-Powered Equipment
- Set-Top Boxes

## Description

The FAN2108 TinyBuck™ is a highly efficient, small footprint, 8 A, synchronous buck regulator.

The FAN2108 contains both synchronous MOSFETs and a controller/driver with optimized interconnects in one package, which enables designers to solve high-current requirements in a small area with minimal external components.

External compensation, programmable switching frequency, and current limit features allow design optimization and flexibility.

The summing current mode modulator uses lossless current sensing for current feedback and over-current protection. Voltage feedforward helps operation over a wide input voltage range.

Fairchild's advanced BiCMOS power process, combined with low- $R_{DS(ON)}$  internal MOSFETs and a thermally efficient MLP package, provide the ability to dissipate high power in a small package.

Output over-voltage, under-voltage, and thermal shutdown protections help protect the device from damage during fault conditions. FAN2108 prevents pre-biased output discharge during startup in point-of-load applications.

## Related Application Notes

[AN-8022 — TinyCalc™ Calculator](#)

## Ordering Information

Part Number	Operating Temperature Range	Package	Packing Method
FAN2108MPX	-10°C to 85°C	Molded Leadless Package (MLP) 5 x 6 mm	Tape and Reel
FAN2108EMPX	-40°C to 85°C		

### Typical Application

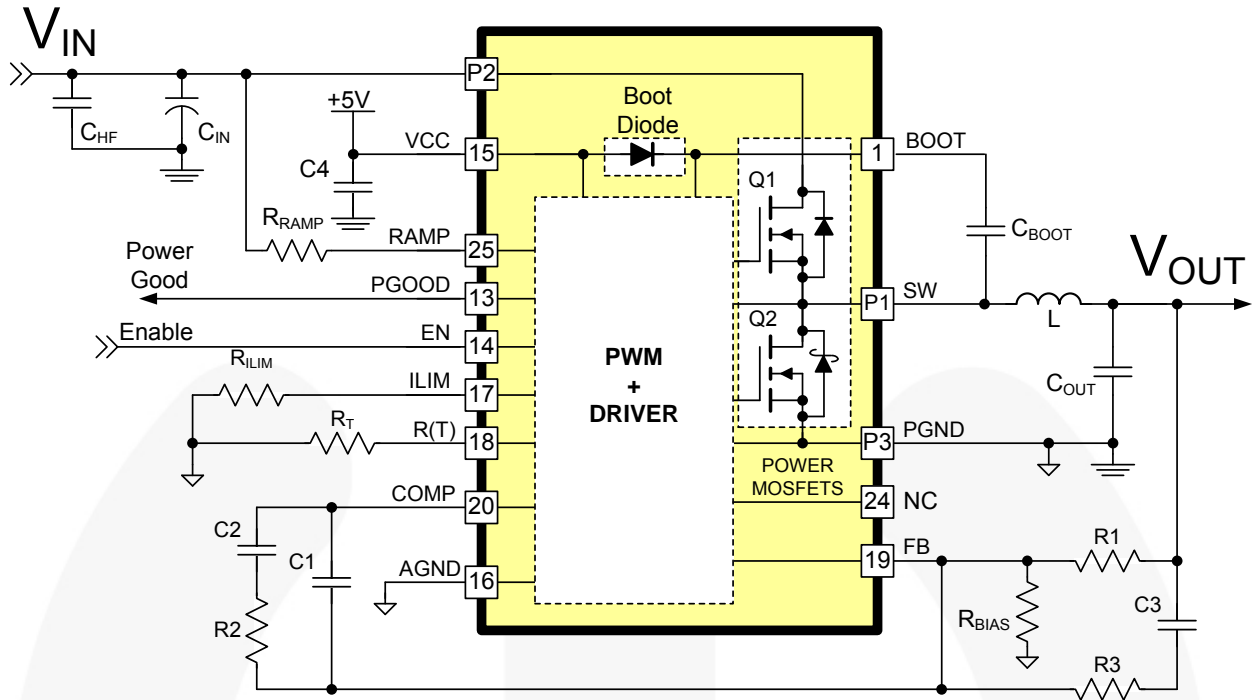


Figure 1. Typical Application Diagram

### Block Diagram

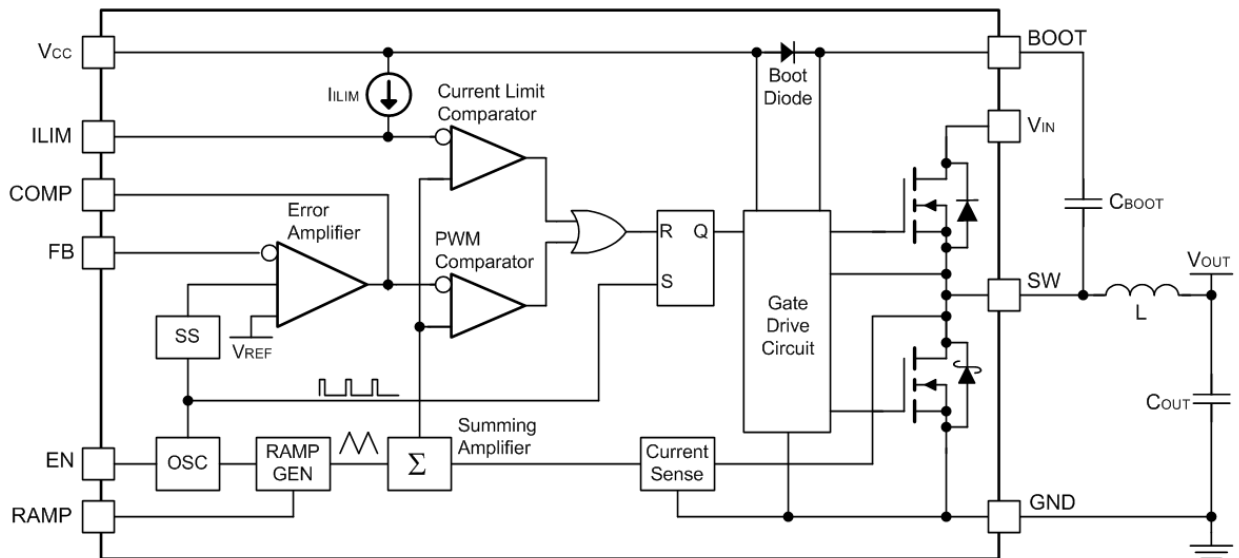


Figure 2. Block Diagram

## Pin Configuration

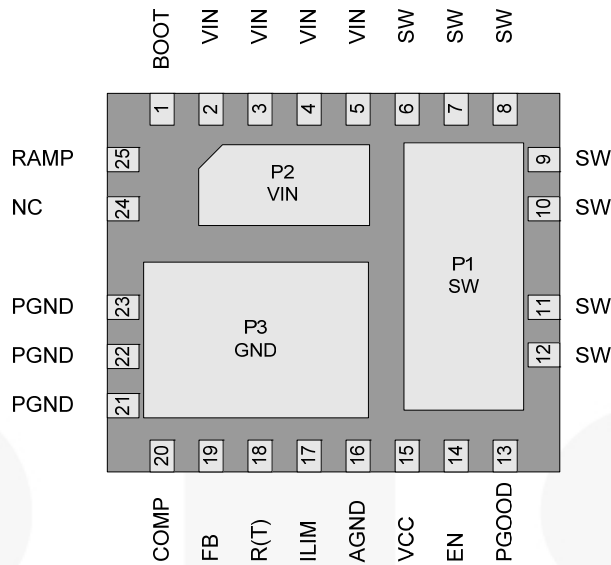


Figure 3. MLP 5 x 6 mm Pin Configuration (Bottom View)

## Pin Definitions

Pin #	Name	Description
P1, 6-12	SW	<b>Switching Node.</b>
P2, 2-5	VIN	<b>Power Input Voltage.</b> Connect to the main input power source.
P3, 21-23	PGND	<b>Power Ground.</b> Power return and Q2 source.
1	BOOT	<b>High-Side Drive BOOT Voltage.</b> Connect through capacitor ( $C_{BOOT}$ ) to SW. The IC includes an internal synchronous bootstrap diode to recharge the capacitor on this pin to $V_{CC}$ when SW is LOW.
13	PGOOD	<b>Power-Good Flag.</b> An open-drain output that pulls LOW when FB is outside a $\pm 10\%$ range of the reference. PGOOD does not assert HIGH until the fault latch is enabled.
14	EN	<b>ENABLE.</b> Enables operation when pulled to logic HIGH or left open. Toggling EN resets the regulator after a latched fault condition. This input has an internal pull-up when the IC is functioning normally. When a latched fault occurs, EN is discharged by a current sink.
15	VCC	<b>Input Bias Supply for IC.</b> The IC's logic and analog circuitry are powered from this pin.
16	AGND	<b>Analog Ground.</b> The signal ground for the IC. All internal control voltages are referred to this pin. Tie this pin to the ground island/plane through the lowest impedance connection.
17	ILIM	<b>Current Limit.</b> A resistor ( $R_{ILIM}$ ) from this pin to AGND can be used to program the current-limit trip threshold lower than the default setting.
18	R(T)	<b>Oscillator Frequency.</b> A resistor ( $R_T$ ) from this pin to AGND sets the PWM switching frequency.
19	FB	<b>Output Voltage Feedback.</b> Connect through a resistor divider to the output voltage.
20	COMP	<b>Compensation.</b> Error amplifier output. Connect the external compensation network between this pin and FB.
24	NC	<b>No Connect.</b> This pin is not used.
25	RAMP	<b>Ramp Amplitude.</b> A resistor ( $R_{RAMP}$ ) connected from this pin to $V_{IN}$ sets the ramp amplitude and provides voltage feedforward functionality.

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Parameter	Conditions	Min.	Max.	Unit
V <sub>IN</sub> to PGND			28	V
V <sub>CC</sub> to AGND	AGND=PGND		6	V
BOOT to PGND			35	V
BOOT to SW		-0.3	6.0	V
SW to PGND	Continuous	-0.5	24.0	V
	Transient (t < 20 ns, f ≤ 600 KHz)	-5	30	V
All other pins		-0.3	V <sub>CC</sub> +0.3	V
ESD	Human Body Model, JEDEC JESD22-A114	2		kV
	Charged Device Model, JEDEC JESD22-C101	2.5		

## Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V <sub>CC</sub>	Bias Voltage	V <sub>CC</sub> to AGND	4.5	5.0	5.5	V
V <sub>IN</sub>	Supply Voltage	V <sub>IN</sub> to PGND	3		24	V
T <sub>A</sub>	Ambient Temperature	FAN2108MPX	-10		+85	°C
		FAN2108EMPX	-40		+85	°C
T <sub>J</sub>	Junction Temperature				+125	°C
f	Switching Frequency				600	kHz

## Thermal Information

Symbol	Parameter	Min.	Typ.	Max.	Unit
T <sub>STG</sub>	Storage Temperature	-65		+150	°C
T <sub>L</sub>	Lead Soldering Temperature, 10 Seconds			+300	°C
T <sub>VP</sub>	Vapor Phase, 60 Seconds			+215	°C
T <sub>I</sub>	Infrared, 15 Seconds			+220	°C
θ <sub>JC</sub>	Thermal Resistance: Junction-to-Case	P1 (Q2)	4		°C/W
		P2 (Q1)	7		°C/W
		P3	4		°C/W
θ <sub>J-PCB</sub>	Thermal Resistance: Junction-to-Mounting Surface <sup>(1)</sup>		35		°C/W
P <sub>D</sub>	Power Dissipation, T <sub>A</sub> =25°C <sup>(1)</sup>			2.8	W

### Note:

1. Typical thermal resistance when mounted on a four-layer, two-ounce PCB, as shown in Figure 25. Actual results are dependent on mounting method and surface related to the design.

## Electrical Specifications

Electrical specifications are the result of using the circuit shown in Figure 1 unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Power Supplies</b>						
$I_{CC}$	$V_{CC}$ Current	SW=Open, FB=0.7 V, $V_{CC}$ =5 V, $f_{SW}$ =600 KHz		8	12	mA
		Shutdown: EN=0, $V_{CC}$ =5 V		7	10	$\mu$ A
$V_{UVLO}$	$V_{CC}$ UVLO Threshold	Rising $V_{CC}$	4.1	4.3	4.5	V
		Hysteresis		300		mV
<b>Oscillator</b>						
f	Frequency	$R_T$ =50 K $\Omega$	255	300	345	KHz
		$R_T$ =24 K $\Omega$	540	600	660	KHz
$t_{ON}$	Minimum On-Time <sup>(2)</sup>			50	65	ns
$V_{RAMP}$	Ramp Amplitude, peak-to-peak	16 $V_{IN}$ , 1.8 $V_{OUT}$ , $R_T$ =30 K $\Omega$ , $R_{RAMP}$ =200 K $\Omega$		0.53		V
$t_{OFF}$	Minimum Off-Time <sup>(2)</sup>			100	150	ns
<b>Reference</b>						
$V_{FB}$	Reference Voltage (see Figure 4 for Temperature Coefficient)	FAN2108MPX, 25°C	794	800	806	mV
		FAN2108EMPX, 25°C	795	800	805	mV
<b>Error Amplifier</b>						
G	DC Gain <sup>(2)</sup>		80	85		dB
BW	Gain Bandwidth Product <sup>(2)</sup>	$V_{CC}$ =5 V	12	15		MHz
$V_{COMP}$	Output Voltage		0.4		3.2	V
$I_{SINK}$	Output Current, Sourcing	$V_{CC}$ =5 V, $V_{COMP}$ =2.2 V	1.5	2.2		mA
$I_{SOURCE}$	Output Current, Sinking	$V_{CC}$ =5 V, $V_{COMP}$ =1.2 V	0.8	1.2		mA
$I_{BIAS}$	FB Bias Current	$V_{FB}$ =0.8 V, 25°C	-850	-650	-450	nA
<b>Protection and Shutdown</b>						
$I_{LIM}$	Current Limit	$R_{ILIM}$ Open at 25°C (see Circuit Description)	12	15	18	A
$I_{LIM}$	$I_{LIM}$ Current		-11	-10	-9	$\mu$ A
$T_{TSD}$	Over-Temperature Shutdown	Internal IC Temperature		+155		°C
$T_{HYS}$	Over-Temperature Hysteresis			+30		°C
$V_{OVP}$	Over-Voltage Threshold	Two Consecutive Clock Cycles	110	115	121	% $V_{OUT}$
$V_{UVLO}$	Under-Voltage Shutdown	16 Consecutive Clock Cycles	68	73	78	% $V_{OUT}$
$V_{FLT}$	Fault Discharge Threshold	Measured at FB Pin		250		mV
$V_{FLT\_HYS}$	Fault Discharge Hysteresis	Measured at FB Pin ( $V_{FB}$ ~500 mV)		250		mV
<b>Soft-Start</b>						
$t_{SS}$	$V_{OUT}$ to Regulation (T0.8)	Frequency=600 KHz		5.3		ms
$t_{EN}$	Fault Enable/SSOK (T1.0)			6.7		ms

**Note:**

2. Specifications guaranteed by design and characterization; not production tested.

## Electrical Specifications (Continued)

Recommended operating conditions are the result of using the circuit shown in Figure 1 unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Control Functions</b>						
$V_{EN\_R}$	EN Threshold, Rising			1.35	2.00	V
$V_{EN\_HYS}$	EN Hysteresis			250		mV
$R_{EN}$	EN Pull-Up Resistance			800		K $\Omega$
$I_{EN}$	EN Discharge Current	Auto-Restart Mode		1		$\mu$ A
$R_{FB}$	FB OK Drive Resistance				800	$\Omega$
$V_{PG}$	PGOOD Threshold	$FB < V_{REF}$	-14	-11	-8	% $V_{REF}$
		$FB > V_{REF}$	+7	+10	+13.5	
$V_{PG\_L}$	PGOOD Output Low	$I_{OUT} \leq 2$ mA			0.4	V

## Typical Characteristics

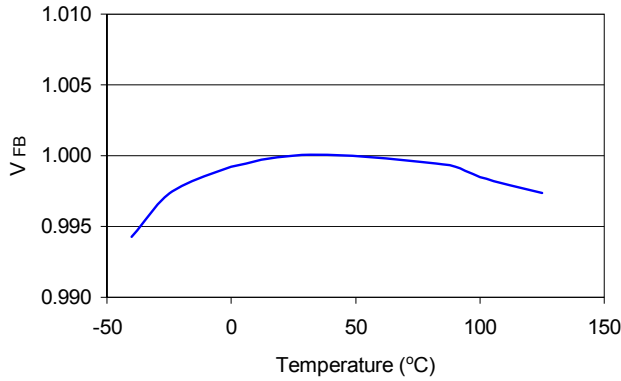


Figure 4. Reference Voltage ( $V_{FB}$ ) vs. Temperature, Normalized

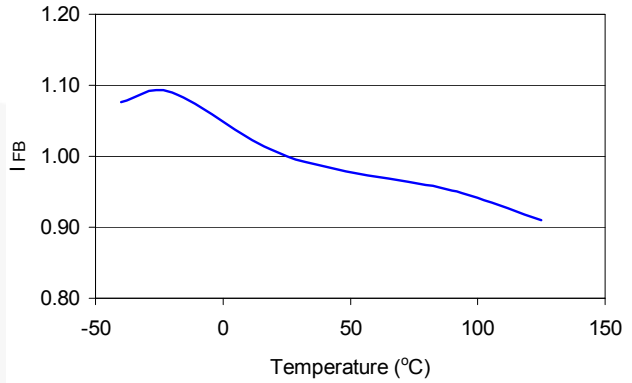


Figure 5. Reference Bias Current ( $I_{FB}$ ) vs. Temperature, Normalized

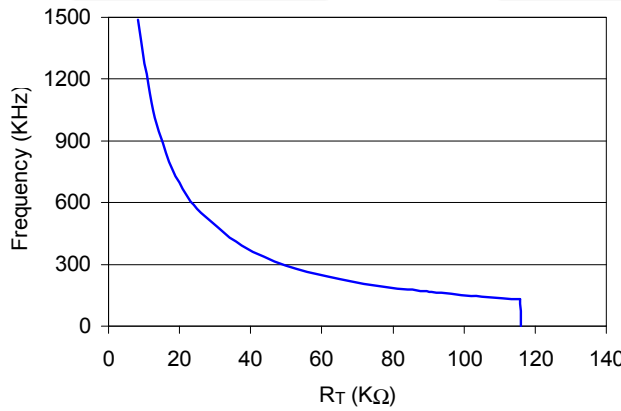


Figure 6. Frequency vs.  $R_T$

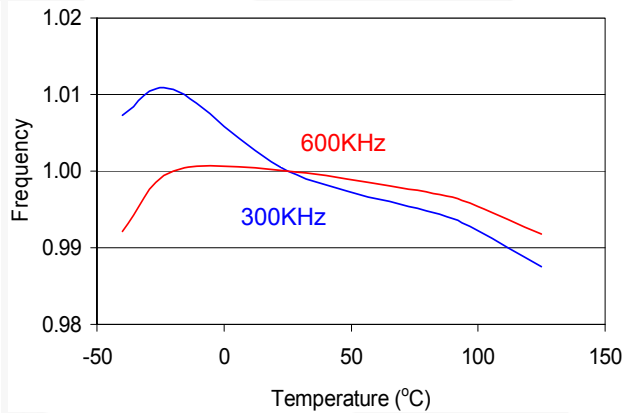


Figure 7. Frequency vs. Temperature, Normalized

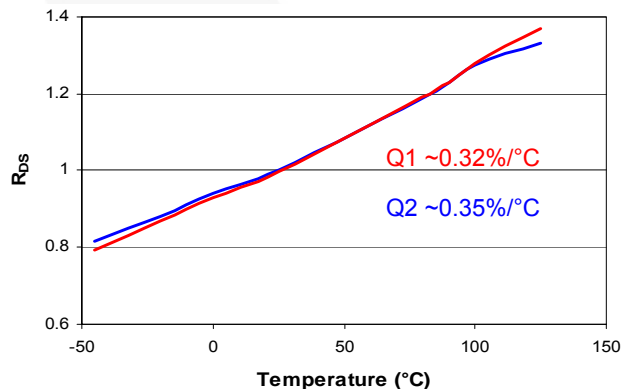


Figure 8.  $R_{DS}$  vs. Temperature, Normalized ( $V_{CC}=V_{GS}=5V$ )

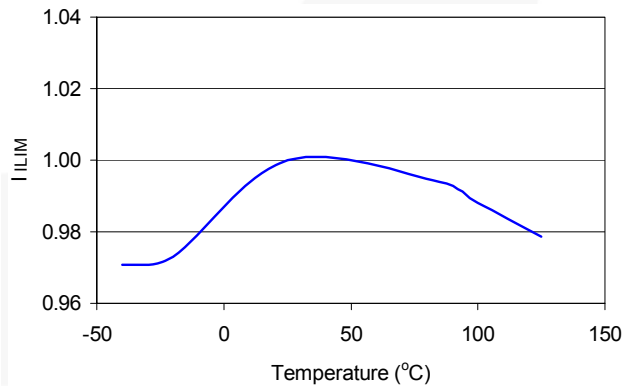


Figure 9.  $I_{LIM}$  Current ( $I_{LIM}$ ) vs. Temperature, Normalized



## Application Circuit

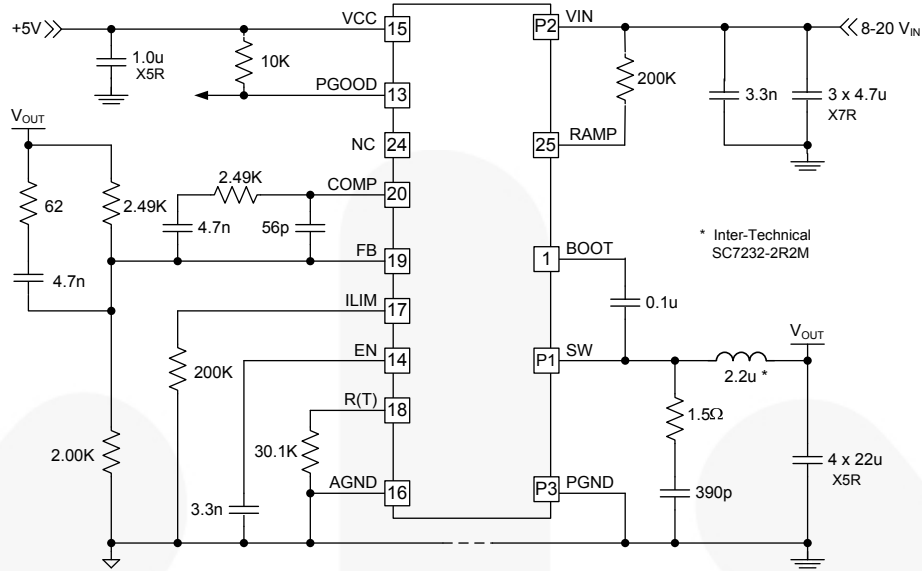


Figure 10. Application Circuit: 1.8 V<sub>OUT</sub>, 500 KHz

## Typical Performance Characteristics

Typical operating characteristics using the circuit shown in Figure 10. V<sub>IN</sub>=12 V, V<sub>CC</sub>=5 V, unless otherwise specified.

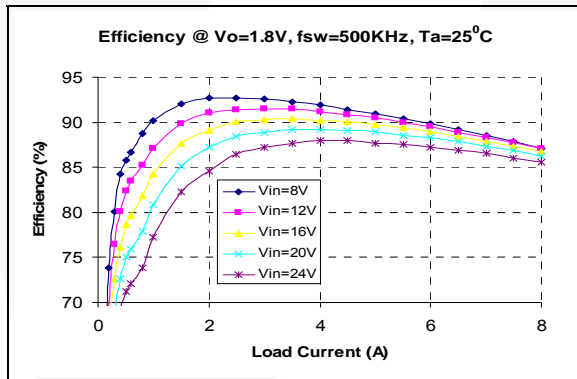


Figure 11. 1.8 V<sub>OUT</sub> Efficiency Over V<sub>IN</sub> vs. Load

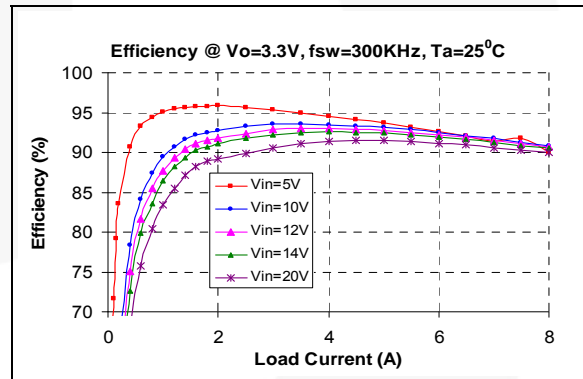


Figure 12. 3.3 V<sub>OUT</sub> Efficiency Over V<sub>IN</sub> vs. Load

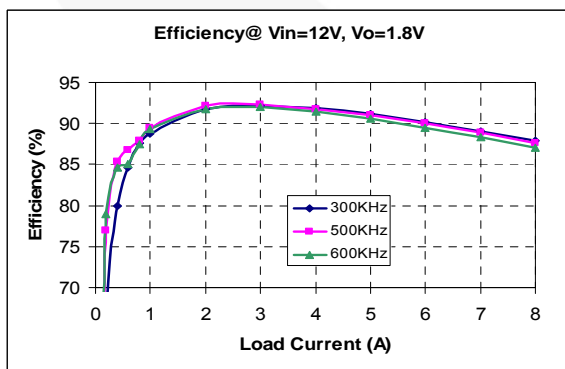


Figure 13. 1.8 V<sub>OUT</sub> Efficiency Over Frequency vs. Load

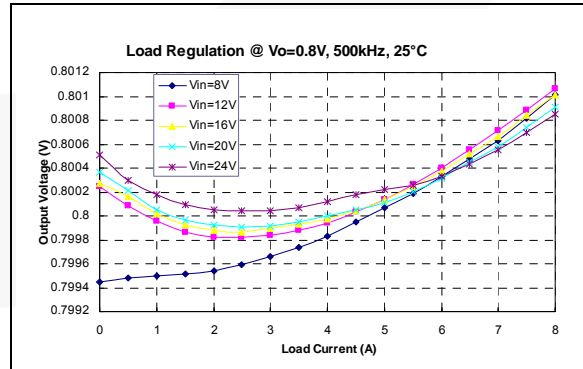


Figure 14. 0.8 V<sub>OUT</sub> Load Regulation Over V<sub>IN</sub> vs. Load

## Typical Performance Characteristics (Continued)

Typical operating characteristics using the circuit shown in Figure 10.  $V_{IN}=12\text{ V}$ ,  $V_{CC}=5\text{ V}$ , unless otherwise specified.

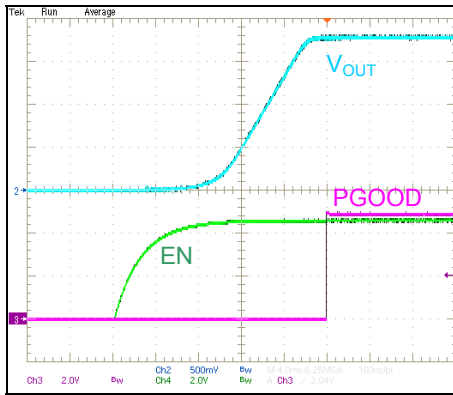


Figure 15. Startup, 3 A Load

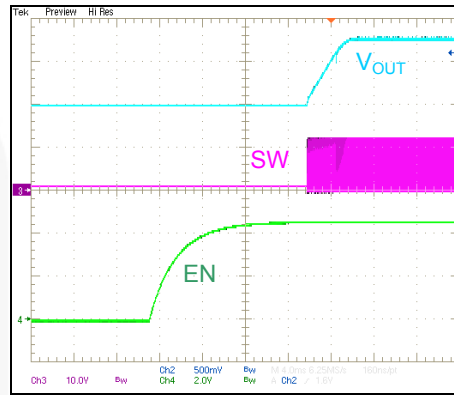


Figure 16. Startup with 1 V Pre-Bias on  $V_{OUT}$

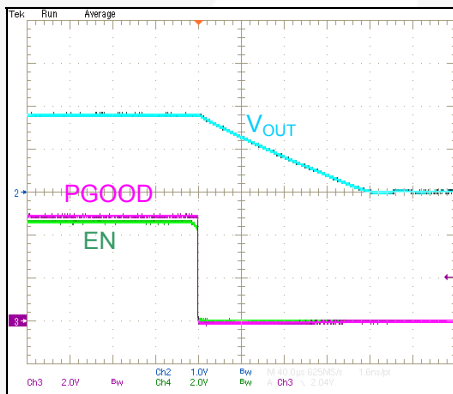


Figure 17. Shutdown, 1 A Load

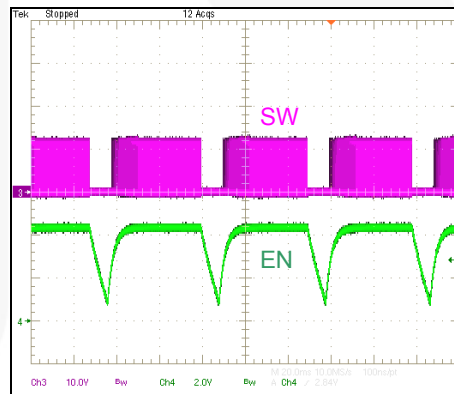


Figure 18. Restart on Fault

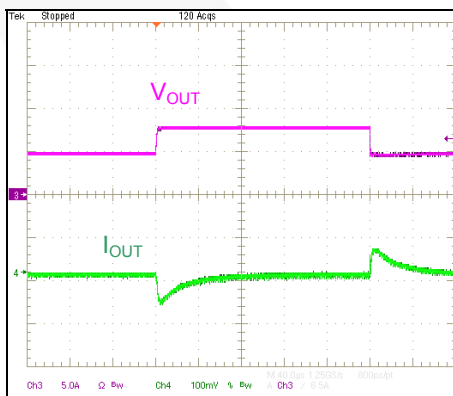


Figure 19. Transient Response, 2-8 A Load

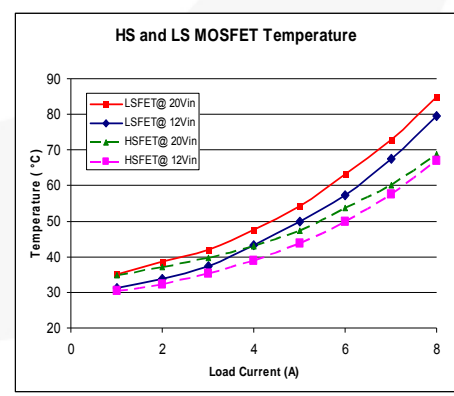


Figure 20. MOSFET Temperature – Still Air at Room Temperature

## Circuit Description

### Initialization

Once  $V_{CC}$  exceeds the UVLO threshold and EN is HIGH, the IC checks for an open or shorted FB pin before releasing the internal soft-start ramp (SS).

If R1 is open (Figure 1), the error amplifier output (COMP) is forced LOW and no pulses are generated. After the SS ramp times out (T1.0), an under-voltage latched fault occurs.

If the parallel combination of R1 and  $R_{BIAS}$  is  $\leq 1\text{ K}\Omega$ , the internal SS ramp is not released and the regulator does not start.

### Bias Supply

The FAN2108 requires a 5 V supply rail to bias the IC and provide gate-drive energy. Connect a  $\geq 1.0\ \mu\text{f}$  X5R or X7R decoupling capacitor between VCC and PGND.

Since  $V_{CC}$  is used to drive the internal MOSFET gates, supply current is frequency and voltage dependent. Approximate  $V_{CC}$  current ( $I_{CC}$ ) is calculated by:

$$I_{CC(mA)} = 4.58 + \left[ \left( \frac{V_{CC} - 5}{227} + 0.013 \right) \cdot (f - 128) \right] \quad (1)$$

where frequency (f) is expressed in KHz.

### Enable

FAN2108 has an internal pull-up to enable pin so that the IC is enabled once  $V_{CC}$  is applied. Connecting a small capacitor across EN and AGND delays the rate of voltage rise on the EN pin. EN pin also serves for the restart whenever a fault occurs (refer to the Auto-Restart section). For applications where sequencing is required, FAN2108 can be enabled (after the  $V_{CC}$  comes up) with external control, as shown in Figure 20.

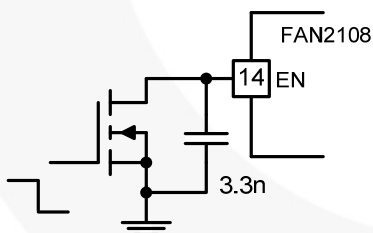


Figure 20. Enabling with External Control

### Setting the Frequency

Oscillator frequency is determined by an external resistor,  $R_T$ , connected between the R(T) pin and AGND. Resistance is calculated by:

$$R_{T(K\Omega)} = \frac{(10^6 / f) - 135}{65} \quad (2)$$

where  $R_T$  is in  $K\Omega$  and frequency (f) is in KHz.

The regulator cannot start if  $R_T$  is left open.

### Soft-Start

Once internal SS ramp has charged to 0.8 V (T0.8), the output voltage is in regulation. Until SS ramp reaches 1.0 V (T1.0), the fault latch is inhibited.

To avoid skipping the soft-start cycle, it is necessary to apply  $V_{IN}$  before  $V_{CC}$  reaches its UVLO threshold.

Soft-start time is a function of oscillator frequency.

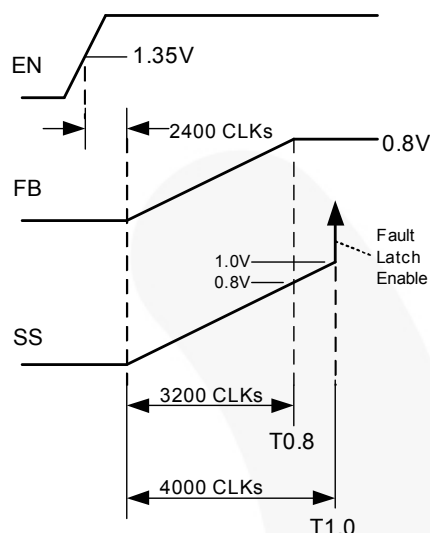


Figure 21. Soft-Start Timing Diagram

The regulator does not allow the low-side MOSFET to operate in full synchronous rectification mode until internal SS ramp reaches 95% of  $V_{REF}$  (~0.76 V). This helps the regulator to start on a pre-biased output and ensures that inductor current does not "ratchet" up during the soft-start cycle.

$V_{CC}$  UVLO or toggling the EN pin discharges the SS and resets the IC.

### Setting the Output Voltage

The output voltage of the regulator can be set from 0.8 V to 80% of  $V_{IN}$  by an external resistor divider ( $R1$  and  $R_{BIAS}$  in Figure 1).

The internal reference is 0.8 V with 650 nA, sourced from the FB pin to ensure that, if the pin is open, the regulator does not start.

The external resistor divider is calculated using:

$$\frac{0.8V}{R_{BIAS}} = \frac{V_{OUT} - 0.8V}{R1} + 650nA \quad (3)$$

Connect  $R_{BIAS}$  between FB and AGND.

### Calculating the Inductor Value

Typically the inductor is set for a ripple current ( $\Delta I_L$ ) of 10% to 35% of the maximum DC load. Regulators requiring fast transient response use a value on the high side of this range; while regulators that require very low output ripple and/or use high-ESR capacitors restrict allowable ripple current.

$$L = \frac{V_{OUT} \cdot (1 - \frac{V_{OUT}}{V_{IN}})}{\Delta I_L \cdot f} \quad (4)$$

where  $f$  is the oscillator frequency.

### Setting the Ramp Resistor Value

The internal ramp voltage excursion ( $\Delta V_{RAMP}$ ) during  $t_{ON}$  should be set to 0.6 V at nominal operating point.  $R_{RAMP}$  is approximately:

$$R_{RAMP(k\Omega)} = \frac{(V_{IN} - 1.8) \cdot V_{OUT}}{18 \times 10^{-6} \cdot V_{IN} \cdot f} - 2 \quad (5)$$

where frequency ( $f$ ) is expressed in KHz.

### Setting the Current Limit

The current limit system involves two comparators. The MAX  $I_{LIMIT}$  comparator is used with a  $V_{ILIM}$  fixed-voltage reference and represents the maximum current limit allowable. This reference voltage is temperature compensated to reflect the  $R_{DSON}$  variation of the low-side MOSFET. The ADJUST  $I_{LIMIT}$  comparator is used where the current limit needs to be set lower than the  $V_{ILIM}$  fixed reference. The 10  $\mu A$  current source does not track the  $R_{DSON}$  changes over temperature, so change is added into the equations for calculating the ADJUST  $I_{LIMIT}$  comparator reference voltage, as is shown below. Figure 22 shows a simplified schematic of the over-current system.

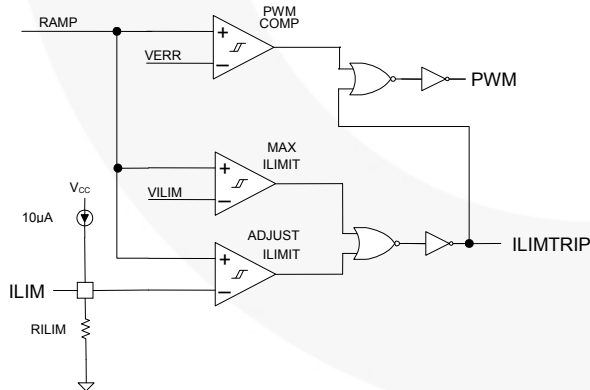


Figure 22. Current-Limit System Schematic

Since the  $I_{LIM}$  voltage is set by a 10  $\mu A$  current source into the  $R_{ILIM}$  resistor, the basic equation for setting the reference voltage is:

$$V_{RILIM} = 10\mu A \cdot R_{ILIM} \quad (6)$$

To calculate  $R_{ILIM}$ :

$$R_{ILIM} = V_{RILIM} / 10\mu A \quad (7)$$

The voltage  $V_{RILIM}$  is made up of two components,  $V_{BOT}$  (which relates to the current through the low-side MOSFET) and  $V_{RMPEAK}$  (which relates to the peak current through the inductor). Combining those two voltage terms results in:

$$R_{ILIM} = (V_{BOT} + V_{RMPEAK}) / 10\mu A \quad (8)$$

$$R_{ILIM} = \{0.96 + (I_{LOAD} \cdot R_{DSON} \cdot K_T \cdot 8)\} + \{D \cdot (V_{IN} - 1.8) / (f_{SW} \cdot 0.03 \cdot 10^{-3} \cdot R_{RAMP})\} / 10\mu A \quad (9)$$

where:

$$V_{BOT} = 0.96 + (I_{LOAD} \cdot R_{DSON} \cdot K_T \cdot 8);$$

$$V_{RMPEAK} = D \cdot (V_{IN} - 1.8) / (f_{SW} \cdot 0.03 \cdot 10^{-3} \cdot R_{RAMP});$$

$I_{LOAD}$  = the desired maximum load current;

$R_{DSON}$  = the nominal  $R_{DSON}$  of the low-side MOSFET;

$K_T$  = the normalized temperature coefficient for the low-side MOSFET (on datasheet graph);

$D = V_{OUT} / V_{IN}$  duty cycle;

$f_{SW}$  = Clock frequency in kHz; and

$R_{RAMP}$  = chosen ramp resistor value in k $\Omega$ .

After 16 consecutive, pulse-by-pulse, current-limit cycles, the fault latch is set and the regulator shuts down. Cycling  $V_{CC}$  or EN restores operation after a normal soft-start cycle (refer to the Auto-Restart section).

The over-current protection fault latch is active during the soft-start cycle. Use 1% resistor for  $R_{ILIM}$ .

### Loop Compensation

The loop is compensated using a feedback network around the error amplifier. Figure 23 shows a complete type-3 compensation network. For type-2 compensation, eliminate  $R_3$  and  $C_3$ .

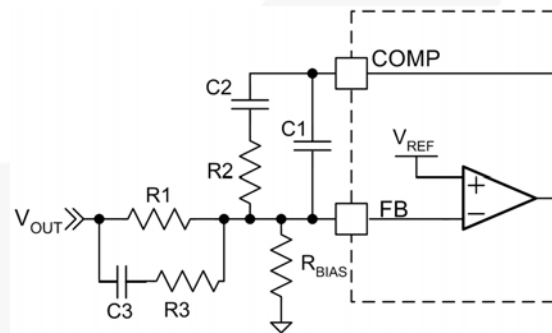


Figure 23. Compensation Network

Since the FAN2108 employs summing current-mode architecture, type-2 compensation can be used for many applications. For applications that require wide loop bandwidth and/or use very low-ESR output capacitors, type-3 compensation may be required.

## Protection

The converter output is monitored and protected against extreme overload, short-circuit, over-voltage, under-voltage, and over-temperature conditions.

An internal fault latch is set for any fault intended to shut down the IC. When the fault latch is set, the IC discharges  $V_{OUT}$  by enhancing the low-side MOSFET until  $FB < 0.25 V$ . The MOSFET is not turned on again unless  $FB > 0.5 V$ . This behavior discharges the output without causing undershoot (negative output voltage).

## Under-Voltage Shutdown

If voltage on the FB pin remains below the under-voltage threshold for 16 consecutive clock cycles, the fault latch is set and the converter shuts down. This protection is not active until the internal SS ramp reaches 1.0 V during soft-start.

## Over-Voltage Protection / Shutdown

If voltage on the FB pin exceeds the over-voltage threshold for two consecutive clock cycles, the fault latch is set and shutdown occurs.

A shorted high-side MOSFET condition is detected when SW voltage exceeds  $\sim 0.7 V$  while the low-side MOSFET is fully enhanced. The fault latch is set immediately upon detection.

The two fault protection circuits above are active all the time, including during soft-start.

## Auto-Restart

After a fault, EN pin is discharged by a  $1 \mu A$  current sink to a 1.1 V threshold before the internal  $800 K\Omega$  pull-up is restored. A new soft-start cycle begins when EN charges above 1.35 V.

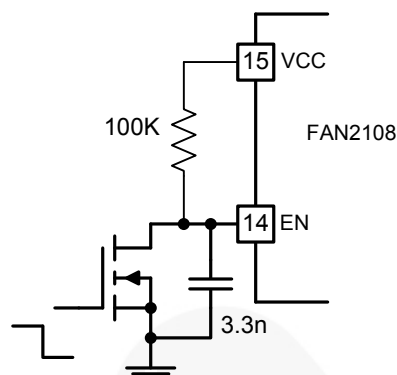
Depending on the external circuit, the FAN2108 can be configured to remain latched-off or to automatically restart after a fault.

**Table 1. Fault / Restart Configurations**

EN Pin	Controller / Restart State
Pull to GND	OFF (Disabled)
Pull-up to $V_{CC}$ with 100K	No Restart – Latched OFF (After $V_{CC}$ Comes Up)
Open	Immediate Restart After Fault
Cap. to GND	New Soft-Start Cycle After: $t_{DELAY} (ms) = 3.9 \cdot C(nf)$

With EN is left open, restart is immediate.

If auto-restart is not desired, tie the EN pin to the VCC pin or pull it HIGH after  $V_{CC}$  comes up with a logic gate to keep the  $1 \mu A$  current sink from discharging EN to 1.1 V. Figure 24 shows one method to pull up EN to  $V_{CC}$  for a latch configuration.



**Figure 24. Enable Control with Latch Option**

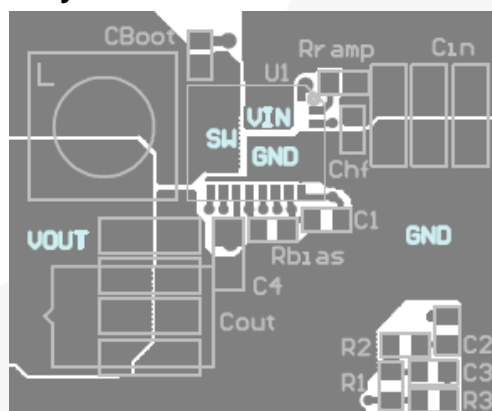
## Over-Temperature Protection (OTP)

The chip incorporates an over-temperature protection circuit that sets the fault latch when a die temperature of about  $150^{\circ}C$  is reached. The IC restarts when the die temperature falls below  $125^{\circ}C$ .

## Power-Good (PGOOD) Signal

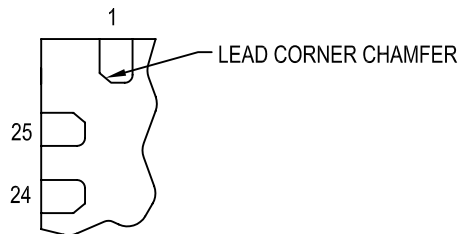
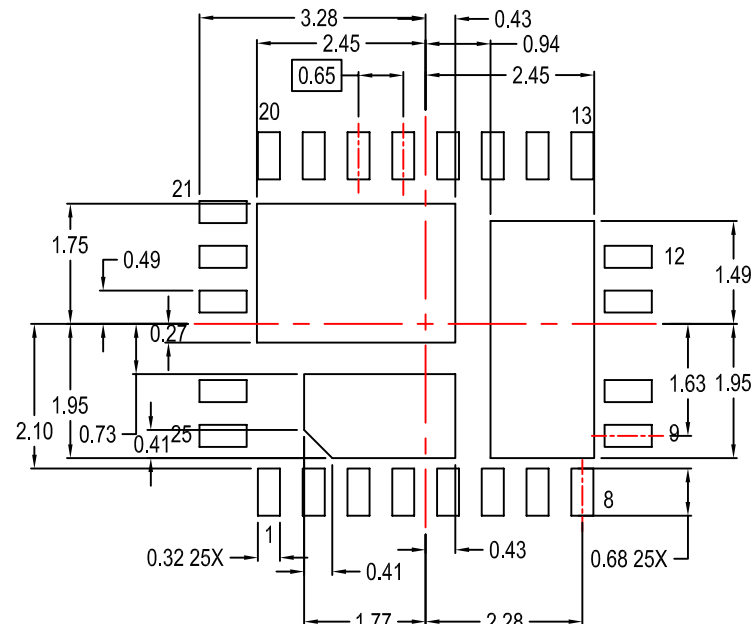
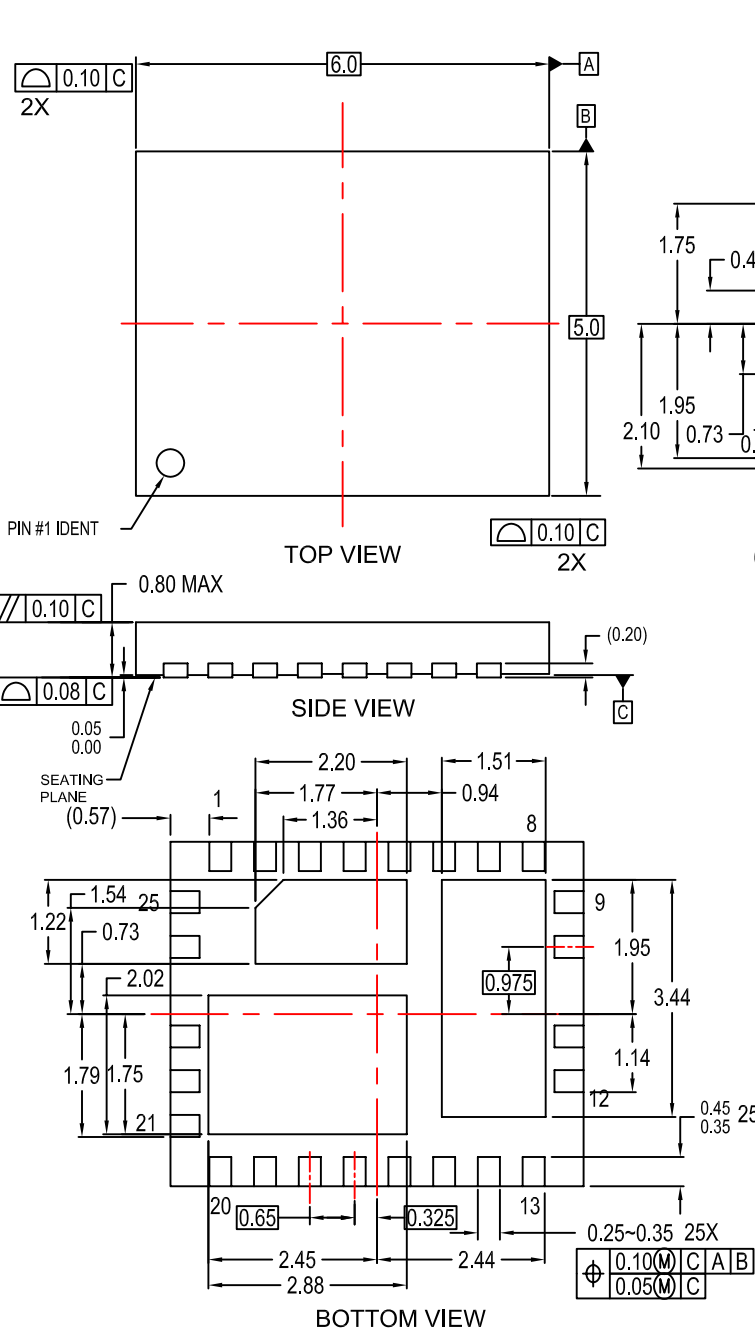
PGOOD is an open-drain output that asserts LOW when  $V_{OUT}$  is out of regulation, as measured at the FB pin. Thresholds are specified in the Electrical Specifications section. PGOOD does not assert HIGH until the fault latch is enabled (T1.0).

## PCB Layout



**Figure 25. Recommended PCB Layout**

REVISIONS			
LTR	DESCRIPTION	DATE	BY/SITE
1	RELEASE TO DOCUMENT CONTROL	12-Jul-2007	J.Chan/FSPM
2	ADDED DIMENSIONS TO BOTTOM VIEW AND LANDPATTERN RECOMMENDATION	7-SEPT-2007	H.ALLEN/FSME
3	CHAMFERED LANDPATTERN PAD 1	17-JUN-2009	H.ALLEN/FSME



- NOTES: UNLESS OTHERWISE SPECIFIED**
- A) DIMENSIONS ARE IN MILLIMETERS.
  - B) DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
  - C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
  - D) DESIGN BASED ON JEDEC MO-220 VARIATION WJHC
  - E) TERMINALS ARE SYMMETRICAL AROUND THE X & Y AXIS EXCEPT WHERE DEPOPULATED.
  - F) DRAWING FILENAME: MKT-MLP25AREV3

APPROVALS		DATE	Bayan Lepas, FIZ, 11900, Penang, Malaysia.
DRAWN	H.ALLEN	7-SEPT-07	
DFTG. CHK.	S.MARTIN	7-SEPT-07	
ENGR. CHK.			
INCH [MM]			SCALE: N/A SIZE: N/A DRAWING NUMBER: MKT-MLP25A REV: 3
			DO NOT SCALE DRAWING SHEET 1 of 1

25LD, MLP, QUAD, NON-JEDEC, 6x5MM TRIPLE DAP

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